## **FEATURES**

- > Complies with JEDEC standard no. 8-1A
- > ESD protection

HBM EIA/JESD22-A114-A exceeds 2000V

MM EIA/JESD22-A115-A exceeds 200V

Specified from -40 to  $+85^{\circ}$ C and -40 to  $+125^{\circ}$ C

## **DESCRIPTION**

The 74HC04/74HCT04 are high-speed Si-gate CMOS devices and are pin compatible with low power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard no. 7A. The 74HC04/74HCT04 provide six inverting buffers.

## **QUICK REFERENCE DATA**

GND = 0V;  $T_{amb} = 25 \,^{\circ}\text{C}$ ;  $t_f = t_f \le 6.0 \text{ns}$ 

SYMBOL	PARAMETER	CONDITIONS	TYF	UNIT	
	TANAMETER	CONDITIONS	HC04	HCT04	UNII
$T_{PLH}/t_{PLH}$	Propagation delay nA to nY	$C_L = 15pF; V_{CC} = 5V$	7	8	ns
$C_{I}$	Input capacitance		3.5	3.4	pF
$C_{PD}$	Power dissipation capacitance per gate	Notes 1 and 2	21	24	pF

#### Notes

1. C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in uW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$  where:

 $f_i$  = input frequency in MHz;

 $f_0$  = output frequency in MHz;

 $C_L$  = output load capacitance in pF;

 $V_{CC}$  = supply voltage in volts;

N = total load switching outputs;

2. For 74HC04: the condition is  $V_I = GND$  to  $V_{CC}$ .

For 74HCT04: the condition is  $V_I = GND$  to  $V_{CC}$ -1.5V

### **FUNCTION TABLE**

#### See note 1.

INPUT	OUTPUT
nA	nY
L	Н
Н	L

#### Note

1. H = HIGH voltage level;

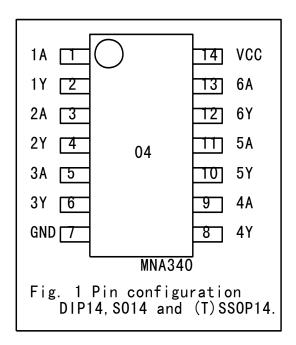
L = LOW voltage level.

## **ORDERING INFORMATION**

TYPE NUMBER		P.	ACKAGE		
I IPE NUMBER	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE
74HC04N	–40 to +125°C	14	DIP14	Plastic	SOT27-1
74HCT04N	–40 to +125°C	14	DIP14	Plastic	SOT27-1
74HC04D	–40 to +125°C	14	SO14	Plastic	SOT108-1
74HCT04D	–40 to +125°C	14	SO14	Plastic	SOT108-1
74HC04DB	–40 to +125°C	14	SSOP14	Plastic	SOT337-01
74HCT04DB	–40 to +125°C	14	SSOP14	Plastic	SOT337-01
74HC04PW	–40 to +125°C	14	TSSOP14	Plastic	SOT402-1
74HCT04PW	–40 to +125°C	14	TSSOP14	Plastic	SOT402-1
74HC04BQ	–40 to +125°C	14	DHVQF14	Plastic	SOT762-1
74HCT04BQ	–40 to +125°C	14	DHVQF14	Plastic	SOT762-1

## **PINNING**

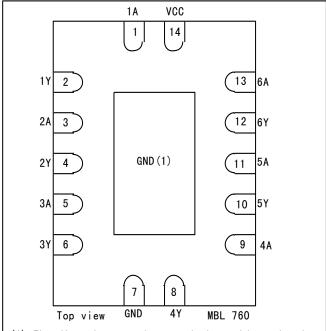
PIN	SYMBOL	DESCRIPTION
1	1A	Data input
2	1Y	Data output
3	2A	Data input
4	2Y	Data output
5	3A	Data input
6	3Y	Data output
7	GND	Ground (0V)
8	4Y	Data output
9	4A	Data input
10	5Y	Data output
11	5A	Data input
12	6Y	Data output
13	6A	Data input
14	VCC	Supply votage





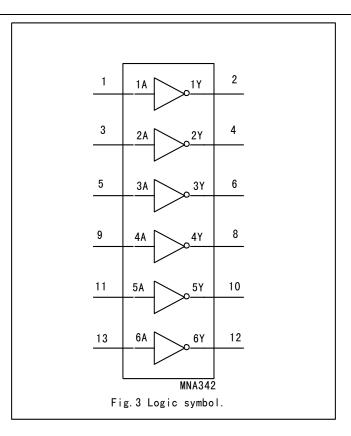
## SHENZHEN FUMAN ELECTRONICS CO., LTD.

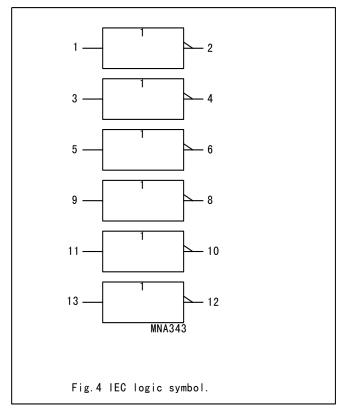
## **74HC04/74HCT04**(文件编号: S&CIC0463)

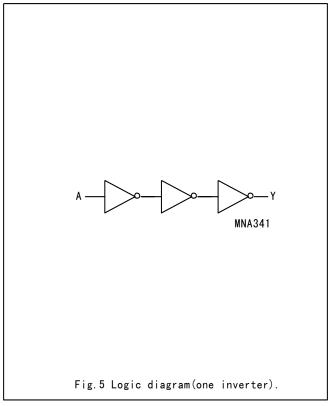


(1) The die substrate is attached to this pad using conductive die attach material.it can not be used as a supply pin or input.

Fig. 2 Pin configuration DHVQFN14.







## RECOMMENDED OPERATING CONDITIONS

CVMDOI	PARAMETER	CONDITIONS		74HC04		74HCT04			UNIT
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNII
VCC	Supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	Input voltage		0	ı	Vcc	0	-	Vcc	V
VO	Output voltage		0	-	Vcc	0	-	Vcc	V
	Ambient temperature	See DC and AC							
Tamb		Characteristics per	-40	+25	+125	-40	+25	+125	$^{\circ}$ C
		Device							
		Vcc = 2.0V	-	-	1000	-	-	-	ns
tr, tf Input rise and fall times	Input rise and fall times	Vcc = 4.5V	-	6.0	500	-	6.0	500	ns
	Vcc = 6.0V	-	-	400	-	-	-	ns	

## LIMITING VALUES

In accordance with the absolute maximum rating system (IEC 60134); voltages are referenced to GND (fround = 0V)

	recordance with the desorate maximum rating system (IDE 60121), votages are referenced to 6112 (fround 617)									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX					
Vcc	Suupply voltage		-0.5	+7.0	V					
$I_{IK}$	Input diode current	$V_{I}$ <-0.5 $V$ <or <math="">V_{I}&lt;<math>V</math>cc+0.5<math>V</math></or>	-	±20	mA					
$I_{OK}$	Output diode currer	$V_{O}$ <-0.5 $V$ <or <math="">V_{O}&lt;<math>V</math>cc+0.5<math>V</math></or>	-	±20	mA					
$I_{O}$	Output source of sink current	-0.5V <v<sub>0<vcc+0.5v< td=""><td>-</td><td>±25</td><td>mA</td></vcc+0.5v<></v<sub>	-	±25	mA					
Icc, I <sub>GND</sub>	Vcc or GND currer		-	±50	mA					
$T_{stg}$	Storage temperature		-65	±150	$^{\circ}\!\mathbb{C}$					
	Power dissipation									
P <sub>tot</sub>	DIP 14 package	$T_{amb} = -40 \text{ to } +125 ^{\circ}\text{C}; \text{ note } 1$	-	750	mW					
	Other packages	$T_{amb} = -40 \text{ to } +125^{\circ}\text{C}; \text{ note } 2$	-	500	mW					

### Notes

1. For DIP14 packages: above  $70^{\circ}$ C derate linearly with 12 mW/K.

2. For SO14 packages: above 70°C derate linearly with 8 mW/K.

For SSOP14 and TSSOP14 packages: above 60°C derate linearly with 5.5mW/K.

For DHVQFN14 packages: above 60°C derate linearly with 4.5mW/K.

## DC CHARACTERISTICS

Type 74HC04

At recommended operating conditions; voltages are referenced to GND (ground = 0V).

CVMDOI	DADAMETED	TEST CONDITIONS		MINI	TYP	MAY	UNIT
SYMBOL	PARAMETER	OTHER	Vcc (V)	MIN	TIP	MAX	UNII
$T_{amb} = 25 ^{\circ}\text{C}$							
			2.0	1.5	1.2	-	V
$V_{\mathrm{IH}}$	HIGH-level input voltage		4.5	3.15	2.4	-	V
			6.0	4.2	3.2	-	V
			2.0	-	0.8	0.5	V
$V_{\mathrm{IL}}$	LOW-level input voltage		4.5	-	2.1	1.35	V
			6.0	-	2.8	1.8	V
	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$					
		$I_{O} = -20uA$	2.0	1.9	2.0	-	V
V		$I_O = -20uA$	4.5	4.4	4.5	-	V
$V_{OH}$		$I_{O} = -4.0 \text{mA}$	4.5	3.98	4.32	-	V
		$I_{O} = -20uA$	6.0	5.9	6.0	-	V
		$I_{O} = -5.2 \text{mA}$	6.0	5.48	5.81	-	V
		$I_O = 20uA$	2.0	-	0	0.1	V
V	LOW-level output voltage	$I_O = 20uA$	4.5	-	0	0.1	V
$V_{OL}$	LOW-level output voltage	$I_{O} = 4.0 uA$	4.5	-	0.15	0.26	V
		$I_{O} = 20uA$	6.0	-	0	0.1	V
		$I_{O} = 5.2uA$	6.0	-	0.16	0.26	V
$I_{LI}$	Input leakage current	$V_I = Vcc \text{ or GND}$	6.0	-	0.1	±0.1	uA
I	3-state output OFF current	$V_{I} = VIH \text{ or VIL};$	6.0		-	±0.5	uA
$I_{OZ}$	3-state output OFF current	$V_0 = Vcc \text{ or GND}$		-	-		u/A
Icc	Quiescent supply current	$V_I = Vcc \text{ or GND}; I_O = 0$	6.0	-	-	2	uA



SYMBOL	PARAMETER	TEST CONDITION	NS	MIN	TYP	MAX	UNIT
SYMBOL	PARAMETER	OTHER	Vcc (V)	MIIN	111	MAA	UNII
$T_{amb} = -40 \text{ to}$	+85°C						
			2.0	1.5	-	-	V
$V_{\mathrm{IH}}$	HIGH-level input voltage		4.5	3.15	1	-	V
			6.0	4.2	-	-	V
			2.0	-	-	0.5	V
$V_{ m IL}$	LOW-level input voltage		4.5	-	-	1.35	V
			6.0	-	-	1.8	V
	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$					
		$I_O = -20uA$	2.0	1.9	-	-	V
$V_{OH}$		$I_O = -20uA$	4.5	4.4	-	-	V
▼ OH		$I_O = -4.0 \text{mA}$	4.5	3.84	-	-	V
		$I_O = -20uA$	6.0	5.9	-	-	V
		$I_O = -5.2 \text{mA}$	6.0	5.34	-	-	V
		$I_O = 20uA$	2.0	-	-	0.1	V
$V_{ m OL}$	LOW-level output voltage	$I_O = 20uA$	4.5	-	1	0.1	V
V <sub>OL</sub>	LOW-level output voltage	$I_{O} = 4.0 uA$	4.5	-	1	0.33	V
		$I_O = 20uA$	6.0	-	1	0.1	V
		$I_O = 5.2uA$	6.0	-	-	0.33	V
$I_{LI}$	Input leakage current	$V_I = Vcc \text{ or GND}$	6.0	-	-	±0.1	uA
$I_{OZ}$	3-state output OFF current	$V_I = VIH \text{ or VIL};$ $V_O = Vcc \text{ or GND}$	6.0	-	-	±5.0	uA
Icc	Quiescent supply current	$V_I = Vcc \text{ or GND}; I_O = 0$	6.0	-	-	20	uA



CVMDOI	PARAMETER	TEST CONDITION	NS	MIN	TYP	MAY	UNIT
SYMBOL	PARAMETER	OTHER	Vcc (V)	IMIIN	TYP	MAX	UNII
$T_{amb} = -40 \text{ to}$	+125℃						
	HIGH-level input voltage		2.0	1.5	-	-	V
$V_{\mathrm{IH}}$			4.5	3.15	-	-	V
			6.0	4.2	-	-	V
			2.0	-	-	0.5	V
$V_{\mathrm{IL}}$	LOW-level input voltage		4.5	-	-	1.35	V
			6.0	-	-	1.8	V
	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$					
		$I_O = -20uA$	2.0	1.9	-	-	V
$V_{\mathrm{OH}}$		$I_O = -20uA$	4.5	4.4	-	-	V
V OH		$I_0 = -20 \text{ uA}$	6.0	5.9	-	-	V
		$I_O = -4.0 \text{mA}$	4.5	3.7	-	-	V
		$I_O = -5.2 \text{mA}$	6.0	5.2	-	-	V
		$I_O = 20uA$	2.0	-	-	0.1	V
$V_{OL}$	LOW-level output voltage	$I_O = 20uA$	4.5	-	-	0.1	V
V OL	LO W-level output voltage	$I_O = 20uA$	6.0	-	-	0.1	V
		$I_{O} = 4.0uA$	4.5	-	-	0.4	V
		$I_{O} = 5.2uA$	6.0	-	-	0.4	V
$I_{LI}$	Input leakage current	$V_I = Vcc \text{ or GND}$	6.0	1	-	±1.0	uA
$I_{OZ}$	3-state output OFF current	$V_I = VIH \text{ or VIL};$ $V_O = Vcc \text{ or GND}$	6.0	-	-	±10.0	uA
Icc	Quiescent supply current	$V_I = Vcc \text{ or } GND; I_O = 0$	6.0	-	-	40	uA



## **Type 74HCT04**

At recommended operating conditions; voltages are referenced to GND (ground = 0V).

CVMDOI	DADAMETED	TEST COND	ITIONS	MINT	TVD	MAV	ן ואוויד
SYMBOL	PARAMETER	OTHER	Vcc (V)	MIN	TYP	MAX	UNIT
$T_{amb} = 25^{\circ}C$							
$V_{\mathrm{IH}}$	HIGH-level input voltage		4.5 to 5.5	2.0	1.6	-	V
$V_{\mathrm{IL}}$	LOW-level input voltage		4.5 to 5.5	1	1.2	0.8	V
		$V_{I} = V_{IH} \text{ or } V_{IL}$					
$V_{OH}$	HIGH-level output voltage	$I_O = -20 \text{ uA}$	4.5	4.4	4.5	-	V
		$I_O = -4.0 \text{mA}$	4.5	3.84	4.32	-	V
		$V_{I} = V_{IH} \text{ or } V_{IL}$					
$V_{OL}$	LOW-level output voltage	$I_O = 20 \text{ uA}$	4.5	-	0	0.1	V
		$I_O = 4.0 \text{mA}$	4.5	-	0.15	0.26	V
$I_{LI}$	Input leakage current	$V_I = Vcc \text{ or GND}$	5.5	-	-	$\pm 0.1$	uA
т.		$V_{I} = V_{IH} \text{ or } V_{IL}$	5.5	-	-	±0.5	uA
$\mathbf{I}_{\mathrm{OZ}}$	I <sub>OZ</sub> 3-state output OFF current	$V_I = Vcc \text{ or } GND$					
		$I_{O} = 0$					
Icc		$V_I = Vcc \text{ or GND}$	5.5	-	-	2	uA
	Quiescent supply current	$I_O = 0$					
Λ.τ.	Abbitional supply current per input	$V_I = Vcc - 2.1V$	4.5 to 5.5	-	120	432	uA
△Icc	Abbitional supply current per input	$I_{O} = 0$					
$T_{amb} = -40 \text{ t}$	to +85 °C						
$V_{IH}$	HIGH-level input voltage		4.5 to 5.5	2.0	-	-	V
$V_{\mathrm{IL}}$	LOW-level input voltage		4.5 to 5.5	-	-	0.8	V
		$V_{I} = V_{IH} \text{ or } V_{IL}$					
$V_{OH}$	HIGH-level output voltage	$I_O = -20 \text{ uA}$	4.5	4.4	-	-	V
		$I_O = -4.0 \text{mA}$	4.5	3.84	-	-	V
		$V_{I} = V_{IH} \text{ or } V_{IL}$					
$V_{OL}$	LOW-level output voltage	$I_0 = 20 \text{ uA}$	4.5	-	-	0.1	V
		$I_O = 4.0 \text{mA}$	4.5	-	-	0.33	V
$I_{LI}$	Input leakage current	$V_I = Vcc \text{ or GND}$	5.5	-	-	±1.0	uA
<u>.</u>		$V_{I} = V_{IH} \text{ or } V_{IL}$	5.5	-	-	±5.0	uA
$I_{OZ}$	3-state output OFF current	$V_I = Vcc \text{ or GND}$					
		$I_{O} = 0$					
T		$V_I = Vcc \text{ or GND}$	<i>5.5</i>			20	
Icc	Quiescent supply current	$I_{O} = 0$	5.5	-	-	20	uA
△Icc	Abbitional supply current per input	$V_{I} = Vcc - 2.1V$ $I_{O} = 0$	4.5 to 5.5	-	-	540	uA



SYMBOL	PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
SIMBOL	TARAWILTER	OTHER	Vcc (V)	IVIIIN	111	WIAA	UNII
$T_{amb} = -40 \text{ t}$	o +125°C						
$V_{\mathrm{IH}}$	HIGH-level input voltage		4.5 to 5.5	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage		4.5 to 5.5	-	-	0.8	V
		$V_{I} = V_{IH} \text{ or } V_{IL}$					
$V_{OH}$	HIGH-level output voltage	$I_O = -20 \text{ uA}$	4.5	4.4	-	-	V
		$I_{O} = -4.0 \text{mA}$	4.5	3.7	-	-	V
	LOW-level output voltage	$V_{\rm I} = V_{\rm IH} \text{ or } V_{\rm IL}$					
$V_{OL}$		$I_O = 20 \text{ uA}$	4.5	-	-	0.1	V
		$I_{O} = 4.0 \text{mA}$	4.5	-	-	0.4	V
$I_{LI}$	Input leakage current	$V_I = Vcc \text{ or GND}$	5.5	-	-	±1.0	uA
т		$V_{\rm I} = V_{\rm IH} \text{ or } V_{\rm IL}$	5.5	-	-	±10	uA
$I_{OZ}$	3-state output OFF current	$V_I = Vcc \text{ or GND}$					
		$I_{O} = 0$					
т		$V_I = Vcc \text{ or GND}$	5.5	-	-	40	uA
Icc	Quiescent supply current	$I_O = 0$					
Λ.τ.	A11.77 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	$V_I = Vcc - 2.1V$	4.5 to 5.5	-	-	590	uA
△Icc	Abbitional supply current per input	$I_O = 0$					

## **AC CHARACTERISTICS**

Family 74HC04

GND = 0V;  $t_r = t_f \le 6.0$ ns;  $C_L = 50$ pF.

CVMDOI	PARAMETER	TEST CONDIT	TEST CONDITIONS		TVD	MAN	LINIT
SYMBOL	PARAMETER	WAVEFORMS	Vcc (V)	MIN	TYP	MAX	UNIT
$T_{amb} = 25^{\circ}\text{C}$							
	Propagation delay nA to nY	See figs 6 and 7	2.0	-	25	85	ns
$t_{\mathrm{PHL}}/t_{\mathrm{PLH}}$			4.5	1	9	17	ns
			6.0	1	7	14	ns
	Output transition time		2.0	1	19	75	ns
$t_{ m THL}/t_{ m TLH}$		See figs 6 and 7	4.5	1	7	15	ns
			6.0	-	6	13	ns
$T_{amb} = -40 \text{ to } +8$	35℃						
	Propagation delay nA to nY		2.0	1	-	105	ns
$t_{\mathrm{PHL}}/t_{\mathrm{PLH}}$		See figs 6 and 7	4.5	1	-	21	ns
			6.0	-	-	18	ns
		See figs 6 and 7	2.0	-	-	95	ns
$t_{THL}/t_{TLH}$	Output transition time		4.5	-	-	19	ns
			6.0	-	-	16	ns
$T_{amb} = -40 \text{ to } +1$	125℃						
	D		2.0	-	-	130	ns
$t_{\mathrm{PHL}}/t_{\mathrm{PLH}}$	Propagation delay nA to nY	See figs 6 and 7	4.5	-	-	26	ns
			6.0	-	-	22	ns
			2.0	-	-	110	ns
$t_{THL}/t_{TLH}$	Output transition time	See figs 6 and 7	4.5	-	-	22	ns
	1		6.0	-	-	19	ns



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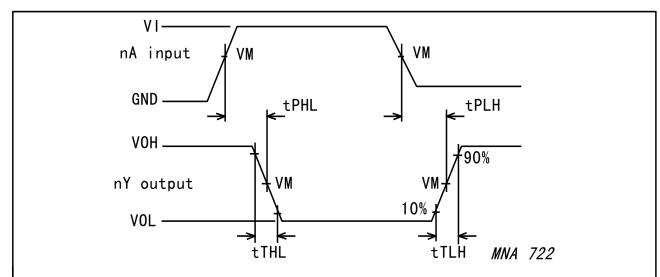
## **74HC04/74HCT04**(文件编号: S&CIC0463)

Family 74HCT04

GND = 0V;  $t_r = t_f \le 6.0$ ns;  $C_L = 50$ pF.

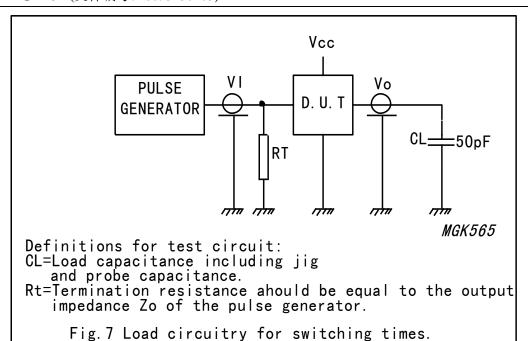
CVMDOL	PARAMETER	TEST CONDIT	IONS	MIN	TYP	MAY	UNIT
SYMBOL	PARAMETER	WAVEFORMS	Vcc (V)	MIN	TIP	MAX	UNII
$T_{amb} = 25 ^{\circ}\text{C}$							
t <sub>PHL</sub> /t <sub>PLH</sub>	Propagation delay nA to nY	See figs 6 and 7	4.5	-	10	19	ns
$t_{THL}/t_{TLH}$	Output transition time	See figs 6 and 7	4.5	-	7	15	ns
$T_{amb} = -40 \text{ to } +85^{\circ}\text{C}$							
t <sub>PHL</sub> /t <sub>PLH</sub>	Propagation delay nA to nY	See figs 6 and 7	4.5	-	-	24	ns
t <sub>THL</sub> /t <sub>TLH</sub>	Output transition time	See figs 6 and 7	4.5	-	-	19	ns
$T_{amb} = -40 \text{ to } +125^{\circ}$	$_{\rm amb} = -40 \text{ to } +125 ^{\circ}\text{C}$						
$t_{ m PHL}/t_{ m PLH}$	Propagation delay nA to nY	See figs 6 and 7	4.5	-	-	29	ns
t <sub>THL</sub> /t <sub>TLH</sub> Output transition time		See figs 6 and 7	4.5	-	-	22	ns

## **AC WAVEFORMS**



For 74HCO4:VM=50%;VI=GND to VCC.
For 74HCTO4:VM=1.3V;VI=GND to 3.0V.
Fig. 6 Waveforms showing the data input(nA) to data output (nY) propagation delays and the output transition times.





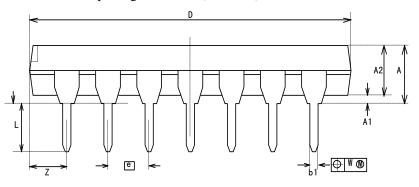


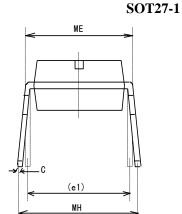
SHENZHEN FUMAN ELECTRONICS CO., LTD.

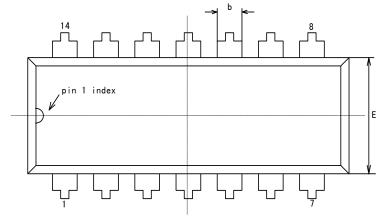
**74HC04/74HCT04**(文件编号: S&CIC0463)

## PACKAGE OUTLINES

DIP 14: plastic dual in-line package; 14 leads (300 minl)







## **DIMENSIONS** (inch dimensions are derived from the original mm dimensions)

UNIT	A	A1	A2	b	B1	с	D <sup>(1)</sup>	E <sup>(1)</sup>	e	$e_1$	L	$M_{\rm E}$	$M_{H}$	W	$Z^{(1)}$
	max	mın	max												max
mm	4.2	0.51	3.2	1.73	0.53	0.36	19.50	6.48	2.54	7.62	3.60	8.25	10.0	0.254	2.2
mm	4.2	0.51	3.2	1.13	0.38	0.23	18.55	6.20	2.34	7.02	3.05	7.80	8.3	0.234	2.2
inahaa	0.17	0.02	0.12	0.068	0.021	0.014	0.77	0.26	0.1	0.2	0.14	0.32	0.39	0.01	0.087
inches	0.17	0.02	0.13	0.044	0.015	0.009	0.73	0.24	0.1	0.3	0.12	0.31	0.33	0.01	0.087

## Note

1. Plastic or metal protrusions of 0.25mm (0.01 inch) maximum per side are not included.

	•		·	•		
OUTLINE		REFE	ERENCES		EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT27-1	050G04	MO-001	SC-201-14			<del></del>

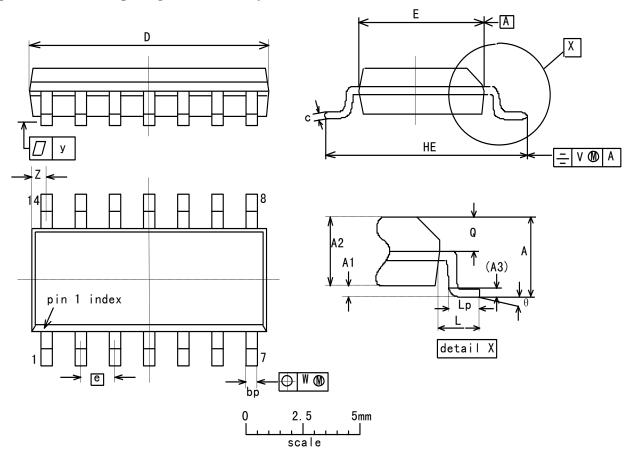


SHENZHEN FUMAN ELECTRONICS CO., LTD.

**74HC04/74HCT04**(文件编号: S&CIC0463)

SO14: plastic small outline package; 14 leads; body width 3.9mm

SOT108-1



## DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A	A1	A2	A3	bp	c	$\mathbf{D}^{(1)}$	E <sup>(1)</sup>	e	$H_{E}$	L	Lp	Q	v	W	у	$\mathbf{Z}^{(1)}$	θ
	max																	
mm	1.75	0.25	1.45	0.25	0.49	0.25	8.75	4.0	1.27	6.2	1.05	1.0	0.7	0.25	0.25	0.1	0.7	
		0.10	1.25		0.36	0.19	8.55	3.8		5.8		0.4	0.6				0.3	8°
inches	0.069	0.010	0.057	0.01	0.019	0.0100	0.35	0.16	0.05	0.244	0.041	0.039	0.028	0.01	0.01	0.004	0.028	0°
		0.004	0.049		0.014	0.0075	0.34	0.15		0.228		0.016	0.024				0.012	

### Note

## 1. Plastic or metal protrusions of 0.15mm (0.006 inch) maximum per side are not included.

OUTLINE		REFE	ERENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT108-1	076E06	MS-012	SC-201-14		<del></del>

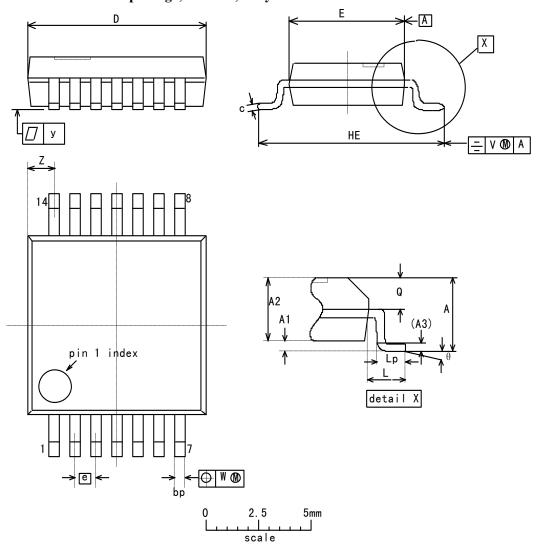


SHENZHEN FUMAN ELECTRONICS CO., LTD.

**74HC04/74HCT04**(文件编号: S&CIC0463)

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3mm

SOT337-1



## DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max	A1	A2	A3	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	e	$H_{E}$	L	Lp	Q	V	W	у	$\mathbf{Z}^{(1)}$	θ
mm	2	0.21	1.80 1.65	0.25	0.38	0.20	6.4	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9	0.2	0.13	0.1	1.4	8° 0°

## Note

1. Plastic or metal protrusions of 0.25mm maximum per side are not included.

OUTLINE		REF	ERENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT337-1		MO-150			<del>- 99-12-27</del> 03-02-19

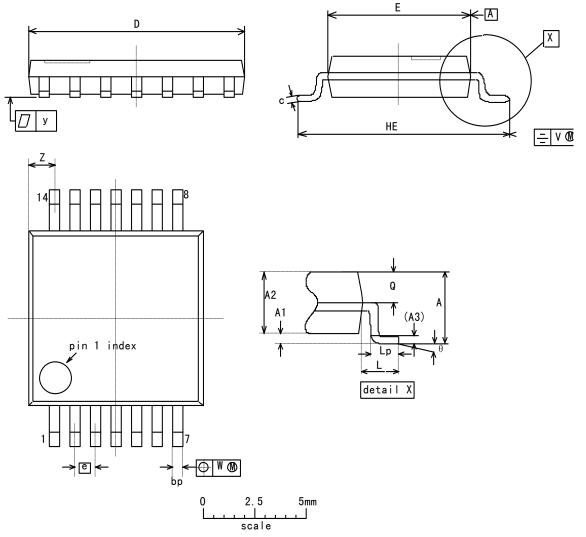


SHENZHEN FUMAN ELECTRONICS CO., LTD.

**74HC04/74HCT04**(文件编号: S&CIC0463)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4mm

SOT402-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A	A1	A2	A3	bp	c	$D^{(1)}$	E <sup>(1)</sup>	e	$H_{E}$	L	Lp	Q	v	W	у	$Z^{(1)}$	θ
	max																	
mm	1.1	0.15	0.95	0.25	0.30	0.2	5.1	4.5	0.65	6.6	1	0.75	0.4	0.2	0.13	0.1	0.72	8°
		0.05	0.80		0.19	0.1	4.9	4.3		6.2		0.50	0.3				0.38	0°

Note: 1. Plastic or metal protrusions of 0.15mm maximum per side are not included.

2. Plastic interlead protrusions of 0.25mm maximum per side are not included.

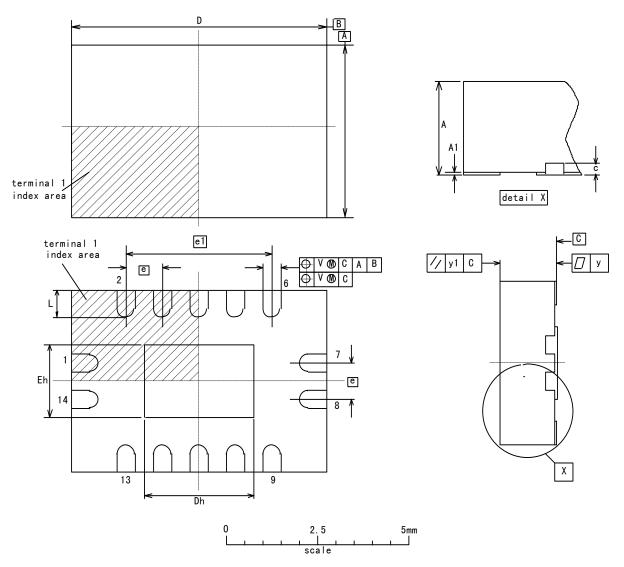
OUTLINE		REFEI	RENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT402-1		MO-153			<del>99-12-27</del> 03-02-18



SHENZHEN FUMAN ELECTRONICS CO., LTD.

**74HC04/74HCT04**(文件编号: S&CIC0463)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body  $2.5 \times 3 \times 0.85$ mm SOT762-1



## DIMENSIONS (mm are the original dimensions)

UNI T	A <sup>(1)</sup> max	A1	b	С	D <sup>(1)</sup>	$D_h$	E <sup>(1)</sup>	$E_h$	e	e1	L	v	w	у	y1
mm	1	0.05 0.00	0.30 0.18	0.2	3.1 2.9	1.65 1.35	2.6 2.4	1.15 0.85	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38

Note: 1. Plastic or metal protrusions of 0.075mm maximum per side are not included.

OUTLINE		REFE	ERENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT762-1		MO-241			<del>-02-10-17-</del> 03-01-27



### **DATA SHEET STATUS**

LEVEL	DATA SHEET	PRODUCT	DEFINITION
LEVEL	STATUS(1)	STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product
			Development.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification.
			Supplementary data will be published at a later date.
III	Product data	Production	This data sheet contains data from the product specification.

#### **Notes**

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

### **DEFINITIONS**

**Short-form specification**-The data in a short-from specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook

**Limiting values definition**-Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

**Application information**-Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

### PAD ASSIGNMENT

	Pad No	Pad Name	X	Y
	1	A1	-243.00	-48.00
A6 Y6 A5 Y5 A4	2	Y1	-243.00	-182.00
	3	A2	-122.50	-182.00
	4	Y2	7.50	-182.00
	5	A3	112.50	-182.00
VDD Y4	6	Y3	242.50	-182.00
	7	VSS	230.50	-57.50
A1 VSS	8	Y4	242.50	47.50
Y1 A2 Y2 A3 Y3	9	A4	242.50	181.50
	10	Y5	122.00	181.50
	11	A5	-8.00	181.50
	12	Y6	-113.00	181.50
	13	A6	-243.00	181.50
	14	VDD	-243.00	57.00